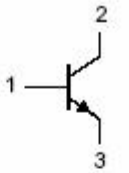
isc Silicon NPN Power Transistor — 2SC1108

DESCRIPTION

- Low Collector Saturation Voltage
- High Current 4A
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

1 2 3



PIN 1. BASE
2.COLLECTOR
3. EMITTER
TO-220C package

APPLICATIONS

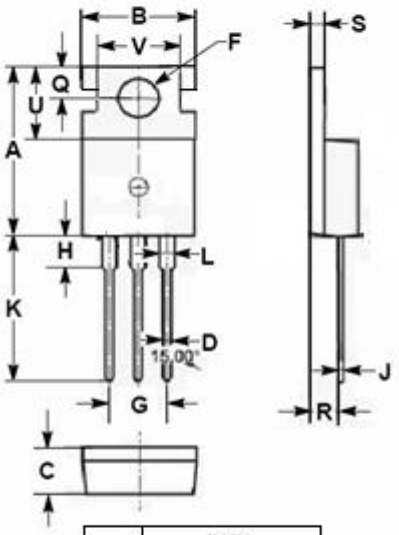
- Designed for use in low frequency power amplifier applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	100	V
V_{CEO}	Collector-Emitter Voltage	100	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	4	A
P_C	Total Power Dissipation @ T_C=25℃	40	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to Case	3.125	℃/W



DIM	mm MIN	mm MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 10mA ; I_B= 0	100			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= 5mA ; I_E= 0	100			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 5mA ; I_C= 0	4			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 3A; I_B= 0.3A			1.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 3A; I_B= 0.3A			2.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 100V ; I_E= 0			100	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			100	μA
h_{FE}	DC Current Gain	I_C= 1A ; V_{CE}= 4V	100		320	
f_T	Current-Gain—Bandwidth Product	I_C= 0.5A; V_{CE}= 12V; f_{test}= 1MHz	10			MHz